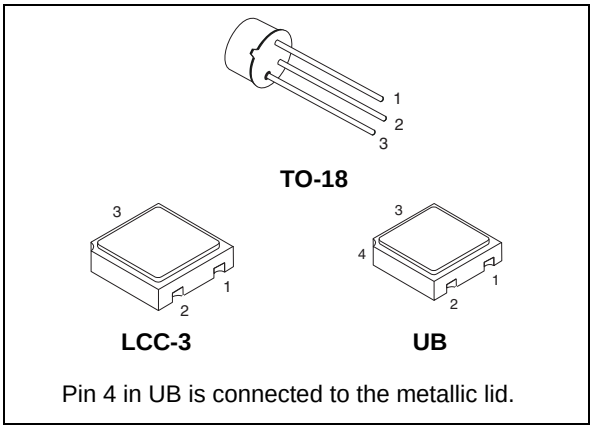
2N2907AHR

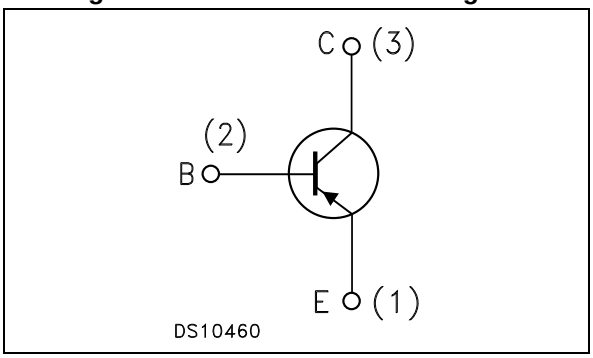
Hi-Rel 60 V, 0.6 A PNP transistor

Datasheet - production data



Pin 4 in UB is connected to the metallic lid.

Figure 1. Internal schematic diagram



Features

Parameter	Value
BV_{CEO}	60 V
I_C (max)	0.6 A
H_{FE} at 10 V - 150 mA	> 100

- Hermetic packages
- ESCC and JANS qualified
- European preferred part list EPPL

Description

The 2N2907AHR is a silicon planar PNP transistor specifically designed and housed in hermetic packages for aerospace and Hi-Rel applications. It is available in the JAN qualification system (MIL-PRF19500 compliance) and in the ESCC qualification system (ESCC 5000 compliance). In case of discrepancies between this datasheet and the relevant agency specification, the latter takes precedence.

Table 1. Device summary

Order codes	Qualification	Agency spec.	Package	Radiation level	EPPL
JANS2N2907AUBx	JANS	MIL-PFR-19500/291	UB	-	-
2N2907AUBxx	ESCC	5202/001		-	Yes
2N2907AUBxxSW35				100 krad SW	Yes
2N2907RUBx				100 krad ESCC	Target
SOC2907AHRB			LCC-3	-	Yes
SOC2907ASW35				100 krad SW	Yes
SOC2907ARHRx				100 krad ESCC	Target
2N2907AHR			TO-18	-	-
2N2907ASW35				100 krad SW	-
2N2907ARHRx				100 krad ESCC	-

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I_E = 0)	-60	V
V_{CEO}	Collector-emitter voltage (I_B = 0)	-60	V
V_{EBO}	Emitter-base voltage (I_C = 0)	-5	V
I_C	Collector current for TO-18 for LCC-3 and UB	 -0.6 -0.5	 A A
P_{TOT}	Total dissipation at $T_{amb} \leq 25$ °C ESCC: TO-18 LCC-3 and UB LCC-3 and UB (1) JANS: UB Total dissipation at $T_{case} \leq 25$ °C ESCC: TO-18	 0.4 0.4 0.73 0.5 1.8	W
	Total dissipation at $T_{sp(IS)}$ = 25 °C JANS: UB	1	
T_{stg}	Storage temperature	-65 to 200	°C
T_J	Max. operating junction temperature	200	°C

1. When mounted on a 15 x 15 x 0.6 mm ceramic substrate.

Table 3. Thermal data

Symbol	Parameter	LCC-3 UB	TO-18	Unit
R_{thJC}	Thermal resistance junction-case (max) for JANS	-	-	°C/W
	Thermal resistance junction-case (max) for ESCC	-	97	
$Rt_{hJSP(IS)}$	Thermal resistance junction-solder pad (infinite sink) (max) for JANS	90	-	
	Thermal resistance junction-solder pad (infinite sink) (max) for ESCC	-	-	
R_{thJA}	Thermal resistance junction-ambient (max) for JANS	325	-	
	Thermal resistance junction-ambient (max) for ESCC	437 240(1)	437	

1. When mounted on a 15 x 15 x 0.6 mm ceramic substrate.

2 Electrical characteristics[(a)]

JANS and ESCC version of the products are assembled and tested in compliance with the agency specification it is qualified in. The electrical characteristics of each version are provided in dedicated tables.

T_{case} = 25 °C unless otherwise specified.

2.1 JANS electrical characteristics

Table 4. JANS electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	V_{CB} = 60 V		-	10	µA
		V_{CB} = 50 V			10	nA
		V_{CB}= 50 V, T_{amb} = 150 °C			10	µA
I_{CES}	Collector cut-off current (I_E = 0)	V_{CE} = 50 V		-	50	nA
I_{EBO}	Emitter cut-off current (I_C = 0)	V_{EB} = 5 V		-	10	µA
		V_{EB} = 4 V			50	nA
$V_{(BR)CEO}$ (1)	Collector-emitter breakdown voltage (I_B = 0)	I_C = 10 mA	60	-		V
$V_{CE(sat)}$ (1)	Collector-emitter saturation voltage	I_C = 150 mA, I_B = 15 mA		-	0.4	V
		I_C = 500 mA, I_B = 50 mA			1.6	V
$V_{BE(sat)}$ (1)	Base-emitter saturation voltage	I_C = 150 mA, I_B = 15 mA	0.6		1.3	V
		I_C= 500 mA, I_B= 50 mA			2.6	V
h_{FE} (1)	DC current gain	I_C = 0.1 mA, V_{CE} = 10 V	75	-		
		I_C = 1 mA, V_{CE} = 10 V	100		450	
		I_C = 10 mA, V_{CE} = 10 V	100			
		I_C = 150 mA, V_{CE} = 10 V	100		300	
		I_C = 500 mA, V_{CE} = 10 V	50			
		I_C = 10 mA, V_{CE} = 10 V T_{amb} = -55 °C	50			
h_{fe}	Small signal current gain	V_{CE} = 20 V I_C = 20 mA f = 100 MHz	2	-		
		V_{CE} = 10 V, I_C =1 mA f = 1 kHz	100			

a. For PNP type, voltage and current values are negative.

Table 4. JANS electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{obo}	Output capacitance (I_E = 0)	V_{CB} = 10 V 100 kHz ≤ f ≤ 1 MHz		-	8	pF
C_{ibo}	Output capacitance (I_E = 0)	V_{EB} = 2 V 100 kHz ≤ f ≤ 1 MHz		-	30	pF
t_{on}	Turn-on time	V_{CC} = 30 V, I_C = 150 mA I_{B1} = 15 mA		-	45	ns
t_{off}	Turn-off time	V_{CC} = 30 V, I_C = 150 mA I_{B1} = -I_{B2} = 15 mA		-	300	ns

1. Pulsed duration = 300 µs, duty cycle ≤ 2%

2.2 ESCC electrical characteristics

Table 5. ESCC electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	V_{CB} = 50 V, V_{CB} = 50 V, T_{amb} = 150 °C		-	10 10	nA µA
$V_{(BR)CBO}$	Collector-base breakdown voltage (I_E = 0)	I_C = 10 µA	60	-		V
$V_{(BR)CEO}$ (1)	Collector-emitter breakdown voltage (I_B = 0)	I_C = 10 mA	60	-		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage (I_C = 0)	I_E = 10 µA	5	-		V
$V_{CE(sat)}$ (1)	Collector-emitter saturation voltage	I_C = 150 mA, I_B = 15 mA		-	0.4	V
$V_{BE(sat)}$ (1)	Base-emitter saturation voltage	I_C = 150 mA, I_B = 15 mA		0.87	1.3	V
h_{FE} (1)	DC current gain	I_C = 0.1 mA, V_{CE} = 10 V	75	-		
		I_C = 10 mA, V_{CE} = 10 V	100			
		I_C = 150 mA, V_{CE} = 10 V	100		300	
		I_C = 500 mA, V_{CE} = 10 V	50			
h_{fe}	Small signal current gain	V_{CE} = 20 V, I_C = 20 mA f = 100 MHz	2	-		
C_{obo}	Output capacitance (I_E = 0)	V_{CB} = 10 V 100 kHz ≤ f ≤ 1 MHz		-	8	pF

Table 5. ESCC electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{on}	Turn-on time	V_{CC} = 30 V, I_C = 150 mA I_{B1} = 15 mA		-	45	ns
t_{off}	Turn-off time	V_{CC} = 30 V, I_C = 150 mA I_{B1} = -I_{B2} = 15 mA		-	300	ns

1. Pulsed duration = 300 µs, duty cycle ≤ 2 %

2.3 Electrical characteristics (curves)

Figure 2. DC current gain (V_{CE} = 1 V)

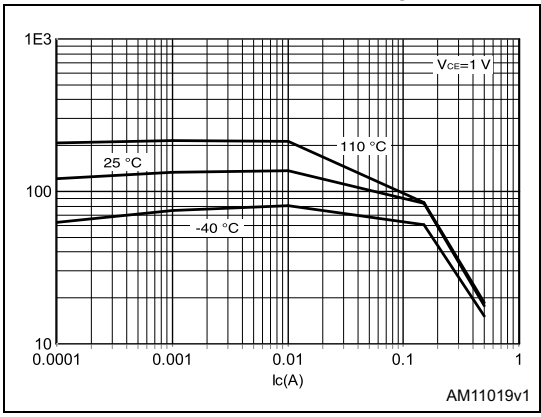


Figure 3. DC current gain (V_{CE} = 10 V)

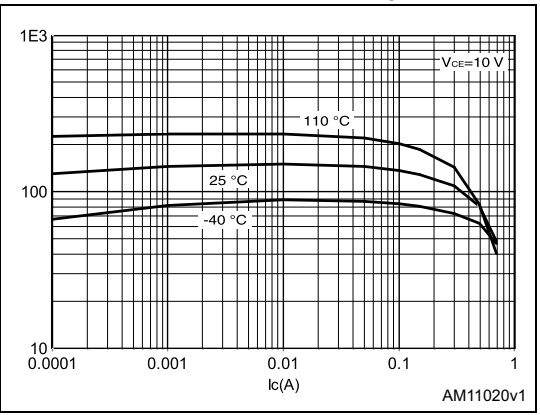


Figure 4. Collector emitter saturation voltage

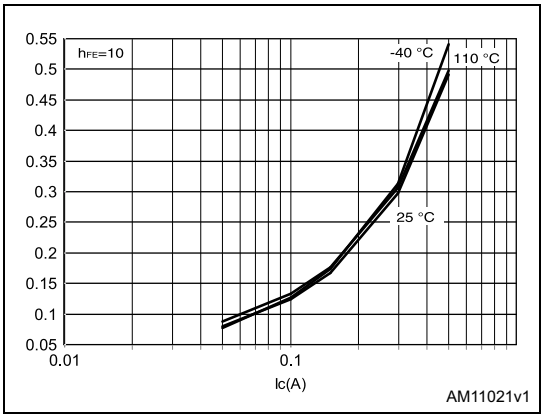
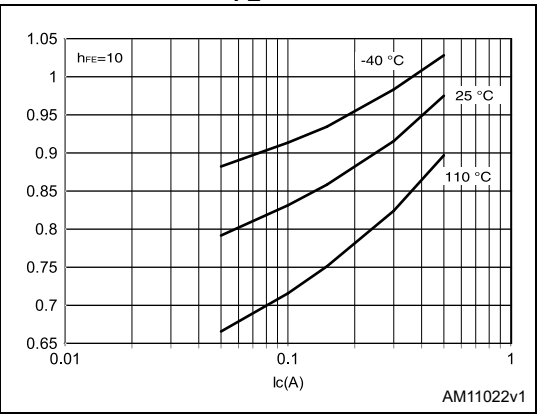
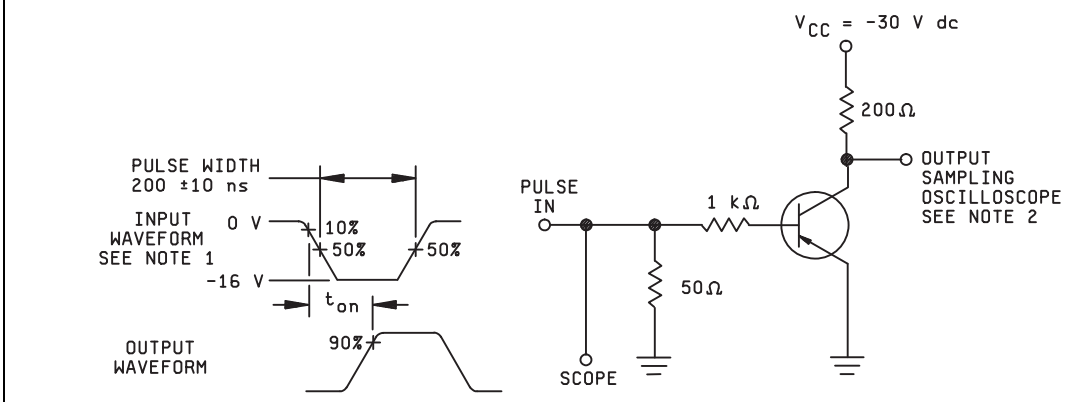


Figure 5. Base emitter saturation voltage (h_{FE} = 10)



2.4 Test circuits

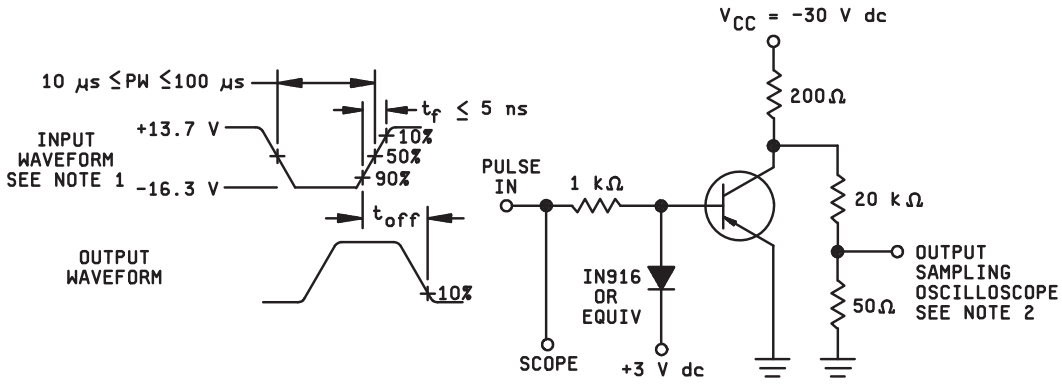
Figure 6. JANS saturated turn-on switching time test circuit



NOTES:

1. The rise time (t_r) of the applied pulse shall be ≤ 2.0 ns, duty cycle ≤ 2 percent and the generator source impedance shall be 50 ohms.
2. Sampling oscilloscope: Z_{in} ≥ 100 K ohms, C_{in} ≤ 12 pF, rise time ≤ 5 ns.

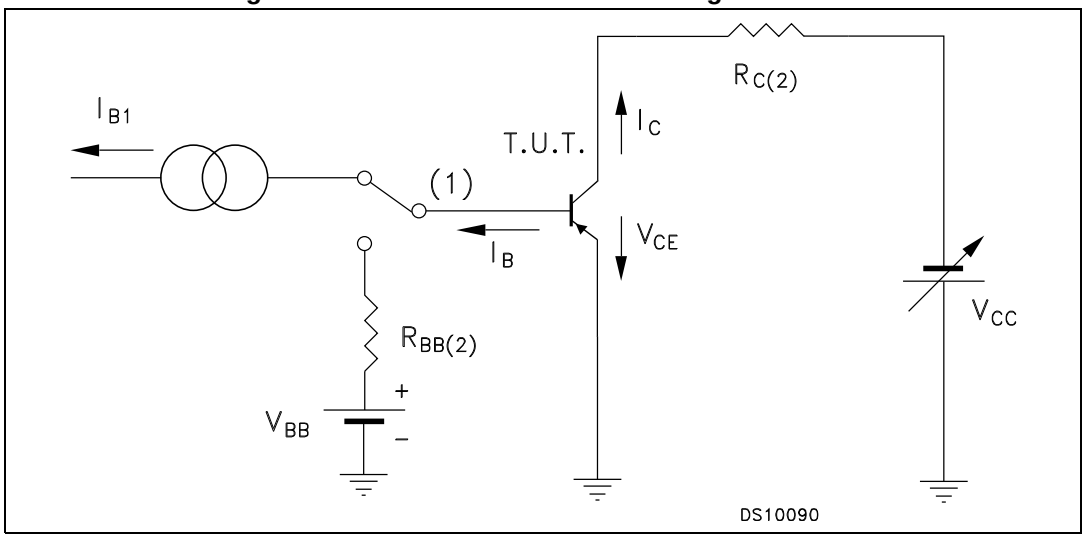
Figure 7. JANS saturated turn-off switching time test circuit



NOTES:

1. The rise time (t_r) of the applied pulse shall be ≤ 2.0 ns, duty cycle ≤ 2 percent and the generator source impedance shall be 50 ohms.
2. Sampling oscilloscope: Z_{in} ≥ 100 K ohms, C_{in} ≤ 12 pF, rise time ≤ 5 ns.

Figure 8. ESCC resistive load switching test circuit



1. Fast electronic switch
2. Non-inductive resistor

3 Radiation hardness assurance[b]

The products guaranteed in radiation within the JANS system fully comply with the MIL-PRF-19500/291 specification.

The products guaranteed in radiation within the ESCC system fully comply with the ESCC 5202/001 and ESCC 22900 specifications.

JANS radiation assurance

ST JANS parts guaranteed at 100 krad (Si), tested, in full compliancy with the MIL-PRF-19500 specification, specifically the Group D, subgroup 2 inspection, between 50 and 300 rad/s. A brief summary is provided below:

– All test are performed in accordance to MIL-PRF-19500 and test method 1019 of MIL-STD-750 for total Ionizing dose.

Each wafer of each lot is tested. The table below provides for each monitored parameters of the test conditions and the acceptance criteria

Table 6. MIL-PRF-19500 (test method 1019) post radiation electrical characteristics

Symbol	Parameter	Test conditions	Value		Unit
			Min.	Max.	
I_{CBO}	Collector to base cutoff current	V_{CB} = 60		20	µA
		V_{CB} = 50 V		20	nA
I_{EBO}	Emitter to base cutoff current	V_{EB} = 5 V		20	µA
		V_{EB} = 4 V		100	nA
$V_{(BR)CEO}$	Breakdown voltage, collector to emitter	I_C = 10 mA	60		V
I_{CES}	Collector to emitter cutoff current	V_{CE} = 50 V		100	nA
h_{FE}	Forward-current transfer ratio	V_{CE} = 10 V; I_C = 0.1 mA	[37.5](1)		
		V_{CE} = 10 V; I_C = 1.0 mA	[50](1)	400	
		V_{CE} = 10 V; I_C = 10 mA	[50](1)		
		V_{CE} = 10 V; I_C = 150 mA	[50](1)	300	
		V_{CE} = 10 V; I_C = 500 mA	[25](1)		
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA		0.46	V
		I_C = 500 mA; I_B = 50 mA		1.84	
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA	0.6	1.5	V
		I_C = 500 mA; I_B = 50 mA		3	

1. See method 1019 of MIL-STD-750 for how to determine [h_{FE}] by first calculating the delta (1/h_{FE}) from the pre- and Post-radiation h_{FE}. Notice the [h_{FE}] is not the same as h_{FE} and cannot be measured directly. The [h_{FE}] value can never exceed the pre-radiation minimum h_{FE} that it is based upon.

b. For PNP type, voltage and current values are negative.

ESCC radiation assurance

Each product lot is tested according to the ESCC basic specification 22900, with a minimum of 11 samples per diffusion lot and 5 samples per wafer, one sample being kept as unirradiated sample, all of them being fully compliant with the applicable ESCC generic and/or detailed specification.

ST goes beyond the ESCC specification by performing the following procedure:

- Test of 11 pieces by wafer, 5 biased at least 80% of $V_{(BR)CEO}$, 5 unbiased and 1 kept for reference
- Irradiation at 0.1 rad (Si)/s
- Acceptance criteria of each individual wafer if as 100 krad guaranteed if all 10 samples comply with the post radiation electrical characteristics provided in *Table 8*.

Delivery together with the parts of the radiation verification test (RVT) report of the particular wafer used to manufacture the products. This RVT includes the value of each parameter at 30, 50, 70 and 100 krad (Si) and after 24 hour annealing at room temperature and after an additional 168 hour annealing at 100°C.

Table 7. Radiation summary

Radiation test	100 krad “SW”	100 krad ESCC
Wafer test	each	each
Part tested	5 biased	5 biased + 5 unbiased
Dose rate	0.1 rad/s	0.1 rad/s
Acceptance	Fixed values (1)	MIL-STD-750 method 1019
Displacement damage	Optional	Optional
Agency part number (ex)	5202/001/04 (2)	5202/001/04R (2)
ST part number (ex)	SOC2N2907ASW35 (1)	SOC2N2907ARHRG
Documents	CoC + RVT	CoC + RVT

1. Part numbers with suffix "SW" have same pre and post irradiation electrical characteristics.
   Part number with suffix "SW35" have specific post irradiation electrical characteristics.
2. Example of the 2N2907A in LCC-3 Gold finish.

Table 8. ESCC 5202/001R post radiation electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current (I_E = 0)	V_{CB} = 50 V		-	10	nA
I_{EBO}	Emitter cut-off current (I_C = 0)	V_{EB} = 3 V		-	10	nA
$V_{(BR)CBO}$	Collector-base breakdown voltage (I_E = 0)	I_C = 10 µA	60	-		V
$V_{(BR)CEO}$ (1)	Collector-emitter breakdown voltage (I_B = 0)	I_C = 10 mA	60	-		V V
$V_{(BR)EBO}$	Emitter-base breakdown voltage (I_C = 0)	I_E = 10 µA	5	-		V
$V_{CE(sat)}$ (1)	Collector-emitter saturation voltage	I_C = 150 mA I_B = 15 mA		-	0.4	V
$V_{BE(sat)}$ (1)	Base-emitter saturation voltage	I_C = 150 mA I_B = 15 mA			1.3	V
$[h_{FE}]$ (1)	Post irradiation gain calculation (2)	I_C = 0.1 mA V_{CE} = 10 V I_C = 10 mA V_{CE} = 10 V I_C = 150 mA V_{CE} = 10 V I_C = 500 mA V_{CE} = 10 V	[75] [100] [100] [50]	-	300	

1. Pulsed duration = 300 µs, duty cycle ≤ 2%
2. The post-irradiation gain calculation of $[h_{FE}]$, made using h_{FE} measurements from prior to and on completion of irradiation testing and after each annealing step if any, shall be as specified in MILSTD-750 method 1019.

Table 9. 2N2907ASW35 post radiation electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CEO}$	Collector-Emitter Breakdown voltage	I_C = 10 mA	60	-	-	V
$V_{(BR)CBO}$	Collector-Base Breakdown voltage	I_E = 10 µA	60	-	-	V
$V_{(BR)EBO}$	Emitter-Base Breakdown voltage	I_E = 10 µA	5	-	-	V
I_{CEX}	Collector-Emitter Cut-off current	V_{CE} = 30 V, V_{EB} = 500 mV	-	-	50	nA
I_{CBO}	Collector-Base Cut-off current	V_{CB} = 50 V	-	-	10	nA
h_{FE1} (1)	Forward-Current Transfer Ratio	V_{CE} = 10 V, I_C = 0.1 mA	50	-	-	-
h_{FE1} (2)		V_{CE} = 10 V, I_C = 0.1 mA	42	-	-	-
h_{FE2}		V_{CE} = 10 V, I_C = 10 mA	100	-	-	-
h_{FE3}		V_{CE} = 10 V, I_C = 150 mA	100	-	300	-
h_{FE4}		V_{CE} = 10V, I_C = 500 mA	50	-	-	-
$V_{CE(sat)}$	Collector-Emitter Saturation voltage	I_C =150 mA, I_B = 15 mA	-	-	400	mV
$V_{BE(sat)}$	Base-Emitter Saturation voltage	I_C = 150 mA, I_B = 15 mA	-	-	1.3	V

1. @ 50 krad (Si)
2. @ 70 krad (Si)

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

Table 10. Product mass summary

Package	Mass (g)
UB	0.06
LCC-3	0.06
TO-18	0.40

Table 11. UB mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	1.16		1.42
C	0.46	0.51	0.56
D	0.56	0.76	0.96
E	0.92	1.02	1.12
F	1.95	2.03	2.11
G	2.92	3.05	3.18
I	2.41	2.54	2.67
J	0.42	0.57	0.72
K	1.37	1.52	1.67
L	0.41	0.51	0.61
M	2.46	2.54	2.62
N	1.81	1.91	2.01
r		0.20	
r1		0.30	
r2		0.56	

Figure 9. UB drawings

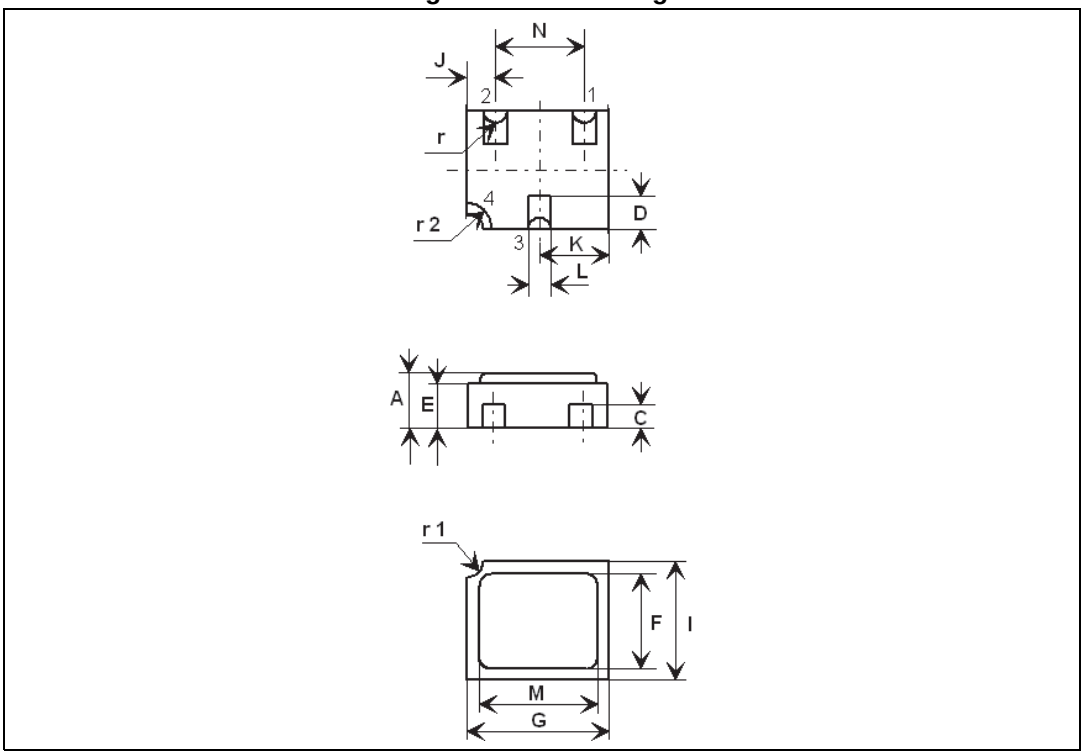


Table 12. LCC-3 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	1.16		1.42
C	0.45	0.50	0.56
D	0.60	0.76	0.91
E	0.91	1.01	1.12
F	1.95	2.03	2.11
G	2.92	3.05	3.17
I	2.41	2.54	2.66
J	0.42	0.57	0.72
K	1.37	1.52	1.67
L	0.40	0.50	0.60
M	2.46	2.54	2.62
N	1.80	1.90	2.00
R		0.30	

Figure 10. LCC-3 drawings

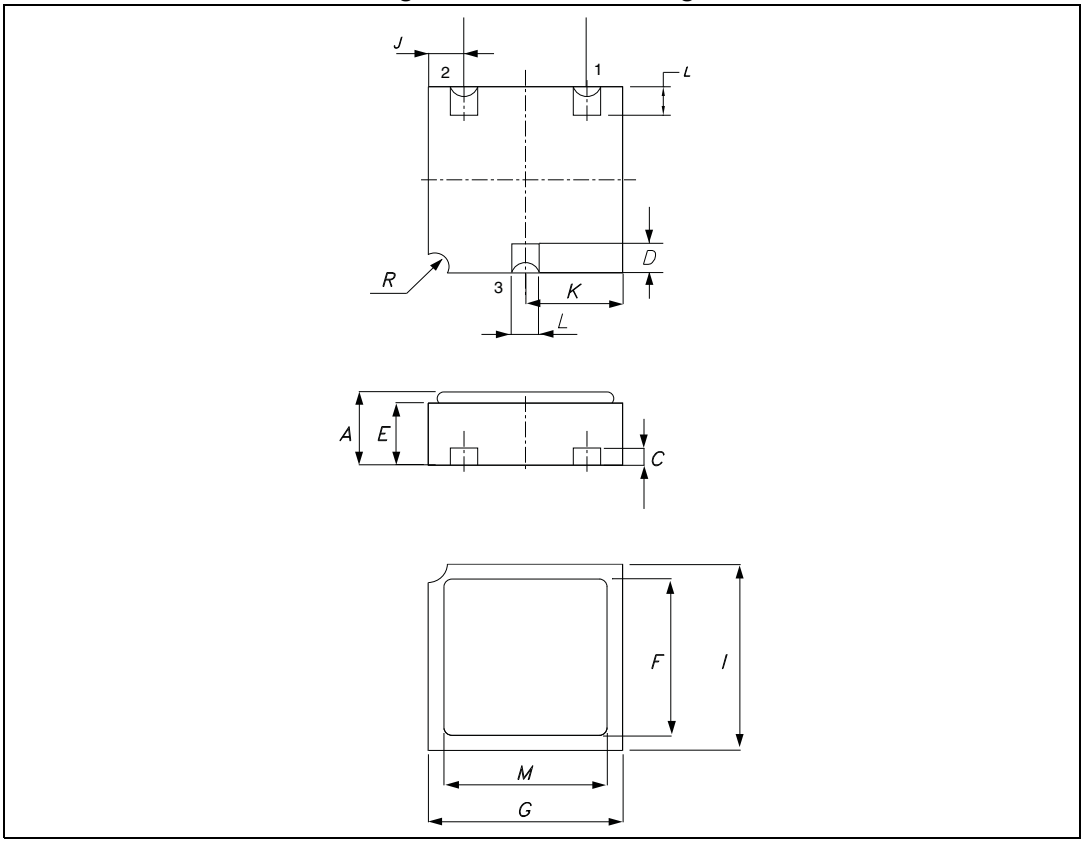
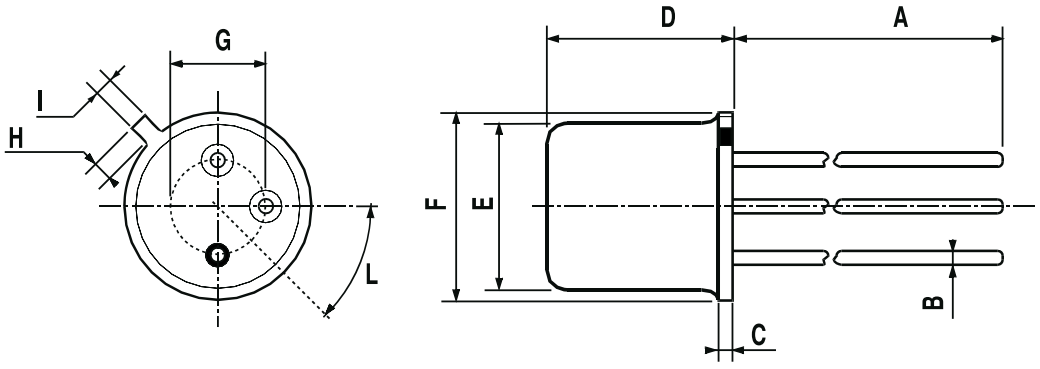


Table 13. TO-18 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A		12.7	
B			0.49
D			5.3
E			4.9
F			5.8
G	2.54		
H			1.2
I			1.16
L	45°		

Figure 11. TO-18 drawings



5 Order codes

Figure 12. Order codes

Part number	Agency specification	EPPL	Quality level	Radiation level	Package	Lead Finish	Marking(1)	Packing
2N2907AUB1	-	-	Engineering model ESCC	-	UB	Gold	U20	Waffle pack
J2N2907AUB1			Engineering model JANS				J2N2907A	
SOC2907A			Engineering model ESCC		LCC-3		N20	
JANS2N2907AUBG	MIL-PRF-19500/291	-	JANS Flight		UB		JS2222	
JANS2N2907AUBT						Solder Dip		
2N2907ARUBG	5202/001/06R	Target	ESCC Flight	100 krad ESCC		Gold	520200406R	
2N2907ARUBT	5202/001/07R	Target				Solder Dip	520200407R	
SOC2907AUB06SW35(2)	5202/001/06	Y		100 krad SW		Gold	520200406	
SOC2907AUB07SW35 (2)	5202/001/07	Y				Solder Dip	520200407	
SOC2907AUB06	5202/001/06			-		Gold	520200406	
SOC2907AUB07	5202/001/07					Solder Dip	520200407	
SOC2907ARHRG	5202/00104R	Target		100 krad ESCC	LCC-3	Gold	520200104R	
SOC2907ARHRT	5202/001/05R	Target				Solder Dip	520200105R	
SOC2907ASW35 (2)	5202/001/04 or 05(3)	Y		100 krad SW		Gold or Solder Dip (1)	520200104 or 05 (3)	
SOC2907AHRB	5202/001/04 or 05 (3)	Y		-				
2N2907AHR	5202/001/01 or 05 (3)				TO-18		520200101 or 05 (3)	Strip pack

1. Specific marking only. The full marking includes in addition:
   For the engineering models: ST logo, date code, country of origin (FR).
   For ESCC flight parts: ST logo, date code, country of origin (FR), ESA logo, serial number of the part within the assembly lot.
   For JANS flight parts: ST logo, date code, country of origin (FR), manufacturer code (CSTM), serial number of the part within the assembly lot.
2. Not recommended for new design
3. Depending ESCC part number mentioned on the purchase order

Contact ST sales office for information about the specific conditions for:

- Products in die form
- Other JANS quality levels
- Tape and reel packing

6 Shipping details

6.1 Date code

Date code xyywwz is structured as below table:

Table 14. Date code

	x	yy	ww	z
EM (ESCC & JANS)	3	last two digits of the year	week digits	lot index in the week
ESCC FLIGHT	-			
JANS FLIGHT (diffused in Singapore)	W			

6.2 Documentation

Table 15. Documentation provided for each type of product

Quality level	Radiation level	Documentation
Engineering model	-	-
JANS Flight	-	Certificate of conformance
JANS Flight	100 krad	Certificate of conformance 50 rad/s radiation verification test report
ESCC Flight	-	Certificate of conformance
ESCC Flight	100 krad	Certificate of conformance 0.1 rad/s radiation verification test report

7 Revision history

Table 16. Document revision history

Date	Revision	Changes
09-Feb-2009	1	Initial release
05-Jan-2010	2	Modified *Table 1 on page 1*
30-Nov-2011	3	Minor text changes in the document title and description on the coverpage
14-May-2012	4	New package inserted (UB). Updated: – *Table 1: Device summary*, *Table 2: Absolute maximum ratings* and *Table 3: Thermal data*. – *Section 2: Electrical characteristics* and *Section 4: Package mechanical data*. Added: – *Section 5: Order codes* and *Section 6: Shipping details*.
03-Jun-2013	5	Added: – new section *Radiation hardness assurance* – *Table 9 on page 12* – Corrected the revision number and dates of revision 3

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